

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

**TC74VHCT540F, TC74VHCT540FW, TC74VHCT540FS  
TC74VHCT541F, TC74VHCT541FW, TC74VHCT541FS****OCTAL BUS BUFFER**TC74VHCT540F / FW / FS INVERTED, 3 - STATE OUTPUTS  
TC74VHCT244F / FW / FS NON - INVERTED, 3 - STATE OUTPUTS

The TC74VHCT540, 541 are advanced high speed CMOS OCTAL BUS BUFFERS fabricated with silicon gate C2MOS technology. They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The TC74VHCT540 is an inverting type and, The TC74VHCT541 is a non-inverting type.

When either  $\bar{G}1$  or  $\bar{G}2$  are high, the terminal outputs are in the high - impedance state.

The input voltage are compatible with TTL output voltage. These devices may be used as a level converter for interfacing 3.3V to 5V system.

Input protection and output circuit ensure that 0 to 7V can be applied to the input and output pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

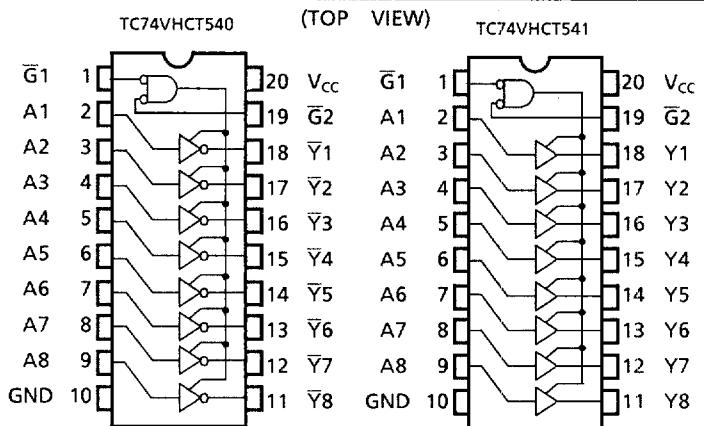
**FEATURES :**

- High Speed .....  $t_{pd} = 5.4\text{ns}(\text{typ.})$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation .....  $I_{CC} = 4\mu\text{A}(\text{Max.})$  at  $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs .....  $V_{IL} = 0.8\text{V} (\text{Max.})$   
 $V_{IH} = 2.0\text{V} (\text{Min.})$
- Power Down Protection is provided on all inputs and outputs
- Balanced Propagation Delays .....  $t_{pLH} \approx t_{pHL}$
- Low Noise .....  $V_{OLP} = 1.6\text{V} (\text{Max.})$
- Pin and Function Compatible with 74ALS540/541

**TRUTH TABLE**

INPUTS			OUTPUTS	
$\bar{G}1$	$\bar{G}2$	$A_n$	$Y_n$	$\bar{Y}_n$
H	X	X	Z	Z
X	H	X	Z	Z
L	L	H	H	L
L	L	L	L	H

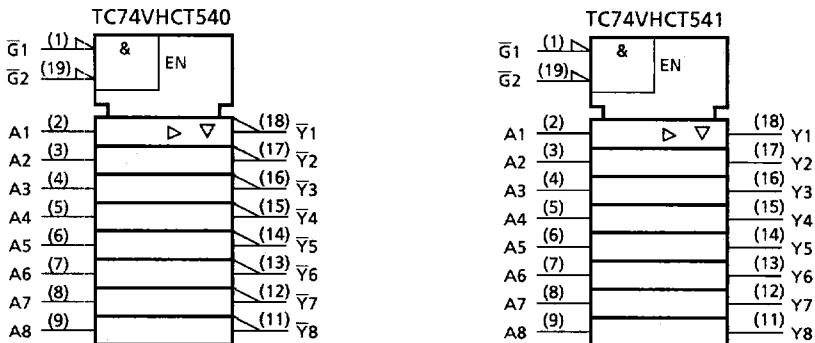
X : Don't Care  
Z : High Impedance  
 $Y_n$  : TC74VHCT541  
 $\bar{Y}_n$  : TC74VHCT540

**PIN ASSIGNMENT**

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## IEC LOGIC SYMBOL



## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7.0	V
DC Input Voltage	$V_{IN}$	-0.5~7.0	V
DC Output Voltage	$V_{OUT}$	-0.5~7.0	V
Input Diode Current	$I_{IK}$	-20	mA
Output Diode Current	$I_{OK}$	-20	mA
DC Output Current	$I_{OUT}$	$\pm 25$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 75$	mA
Power Dissipation	$P_D$	180	mW
Storage Temperature	$T_{STG}$	-65~150	°C

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	4.5~5.5	V
Input Voltage	$V_{IN}$	0~5.5	V
Output Voltage	$V_{OUT}$	0~5.5	V
Operating Temperature	$T_{OPR}$	-40~85	°C
Input Rise and Fall Time	$dt/dV$	0~20	ns/V

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## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITON	V <sub>CC</sub> (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V <sub>IH</sub>		4.5~5.5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V <sub>IL</sub>		4.5~5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50μA	4.5	3.15	3.65	—	3.15	V
			I <sub>OH</sub> = -8mA	4.5	2.50	—	—	2.40	
Low - Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50μA	4.5	—	0.0	0.10	—	V
			I <sub>OL</sub> = 8mA	4.5	—	—	0.36	—	
3 - State Output Off - State Current	I <sub>OZ</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND	5.5	—	—	±0.25	—	±2.50	μA
Input Leakage Current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5V or GND	0~5.5	—	—	±0.1	—	±1.0	
Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	—	—	4.0	—	40.0	mA
	I <sub>CCT</sub>	PER INPUT : V <sub>IN</sub> = 3.4V OTHER INPUT : V <sub>CC</sub> or GND	5.5	—	—	1.35	—	1.50	
Output Leakage Current	I <sub>OPD</sub>	V <sub>OUT</sub> = 5.5V	0	—	—	+0.5	—	+5.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3ns)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time (TC74VHCT540)	t <sub>pLH</sub> t <sub>pHL</sub>	5.0 ± 0.5	15	—	5.4	7.4	1.0	8.5	ns
			50	—	5.9	8.4	1.0	9.5	
Propagation Delay Time (TC74VHCT541)	t <sub>pLH</sub> t <sub>pHL</sub>	5.0 ± 0.5	15	—	5.0	6.9	1.0	8.0	
			50	—	5.5	7.9	1.0	9.0	
3-State Output Enable Time	t <sub>pZL</sub> t <sub>pZH</sub>	R <sub>L</sub> = 1kΩ 5.0 ± 0.5	15	—	8.3	11.3	1.0	13.0	
			50	—	8.8	12.3	1.0	14.0	
3-State Output Disable Time	t <sub>pLZ</sub> t <sub>pHZ</sub>	R <sub>L</sub> = 1kΩ	5.0 ± 0.5	50	—	9.4	11.9	1.0	13.5
Output to Output Skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note 1)	5.0 ± 0.5	50	—	—	1.0	—	1.0
Input Capacitance	C <sub>IN</sub>			—	4	10	—	10	pF
Output Capacitance	C <sub>OUT</sub>			—	9	—	—	—	
Power Dissipation Capacitance	C <sub>PD</sub>	(Note 2)		—	19	—	—	—	

Note (1) Parameter guaranteed by design.  $t_{psLH} = t_{pLHm} - t_{pLHn}$ ,  $t_{osHL} = t_{pHLM} - t_{pHLn}$

Note (2) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

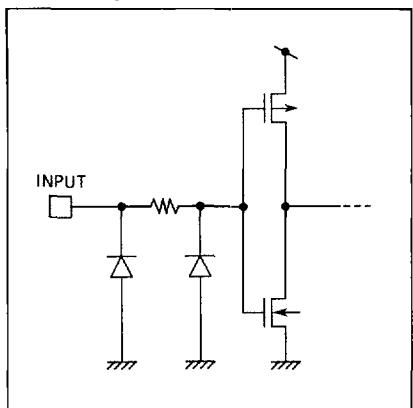
Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

NOISE CHARACTERISTICS ( Input  $t_r = t_f = 3\text{ns}$  )

PARAMETER	SYMBOL	TEST CONDITION		$T_a = 25^\circ\text{C}$		UNIT
			$V_{CC} (\text{V})$	TYP.	LIMIT	
Quiet Output Maximum Dynamic $V_{OL}$	$V_{OLP}$	$C_L = 50\text{pF}$	5.0	1.2	1.6	V
Quiet Output Minimum Dynamic $V_{OL}$	$V_{OLV}$	$C_L = 50\text{pF}$	5.0	-1.2	-1.6	V
Minimum High Level Dynamic Input Voltage	$V_{IHD}$	$C_L = 50\text{pF}$	5.0	-	2.0	V
Maximum Low Level Dynamic Input Voltage	$V_{ILD}$	$C_L = 50\text{pF}$	5.0	-	0.8	V

INPUT EQUIVALENT CIRCUIT



OUTPUT EQUIVALENT CIRCUIT

